



Features

- Operation Frequency: 13.5~14.75GHz
- ACPR: -29dBc@P_{OUT}=36dBm
- Output P₁dB: 38dBm
- VD=+7V~+8V
- Small size: 6mm×6 mm×1.1 mm

Applications

- SATCOM
- Telecom infrastructure
- Military
- Test instrumentation
- Microwave radio

Description

The XT3110Q6 is Ku Band GaAs MMIC power amplifier which operates from 13.5 to 14.75GHz. It provides 29 dB of small signal gain, and 38dBm of output power at 1 dB gain compression. XT3110Q6 is ideal for SATCOM and test equipment applications.

Electrical Specifications (T_A=+25°C, 50Ω)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Output P ₁ dB	P ₁ dB	VD=+7V VGS=-0.8V* f=13.5GHz~ 14.75GHz Pin=-30dBm	36	38	-	dBm
Small Signal Gain	G _S		26	29	-	dB
SS Gain Flatness	Δ G _S		-	± 1.5	-	dB
Quiescent Drain Current	IDQ		-	2.2	2.6	A
Drain Voltage	VD		7	-	8	V
Input Return Loss	RL _i		-	-12	-	dB
Power Added Efficiency	PAE	P _{OUT} = P ₁ dB	-	30	-	%
ACPR Performance**	ψ	P _{OUT} =36dBm	-	-29.5	-	dBc
		P _{OUT} =36.5dBm		-27	-	dBc
		P _{OUT} =37dBm		-26.5	-	dBc
ACPR Performance ***		P _{OUT} =36dBm	-	-30.5	-	dBc
		P _{OUT} =36.5dBm	-	-27.5	-	dBc
		P _{OUT} =37dBm	-	-27.2	-	dBc
EVM Performance **	Π	P _{OUT} =36dBm	-	6.2	-	%
		P _{OUT} =36.5dBm	-	6.5	-	%
		P _{OUT} =37dBm	-	6.5	-	%
EVM Performance ***		P _{OUT} =36dBm	-	5.5	-	%
		P _{OUT} =36.5dBm	-	6	-	%
		P _{OUT} =37dBm	-	6.4	-	%
Thermal Resistance	R _{th}	Tbase=70°C	-	4.1	-	°C/W

* IDQ=2.25A

** f=14.25GHz, VDS=7V, IDQ=2.25A, 8PSK, σ=0.5, symbol rate=2M

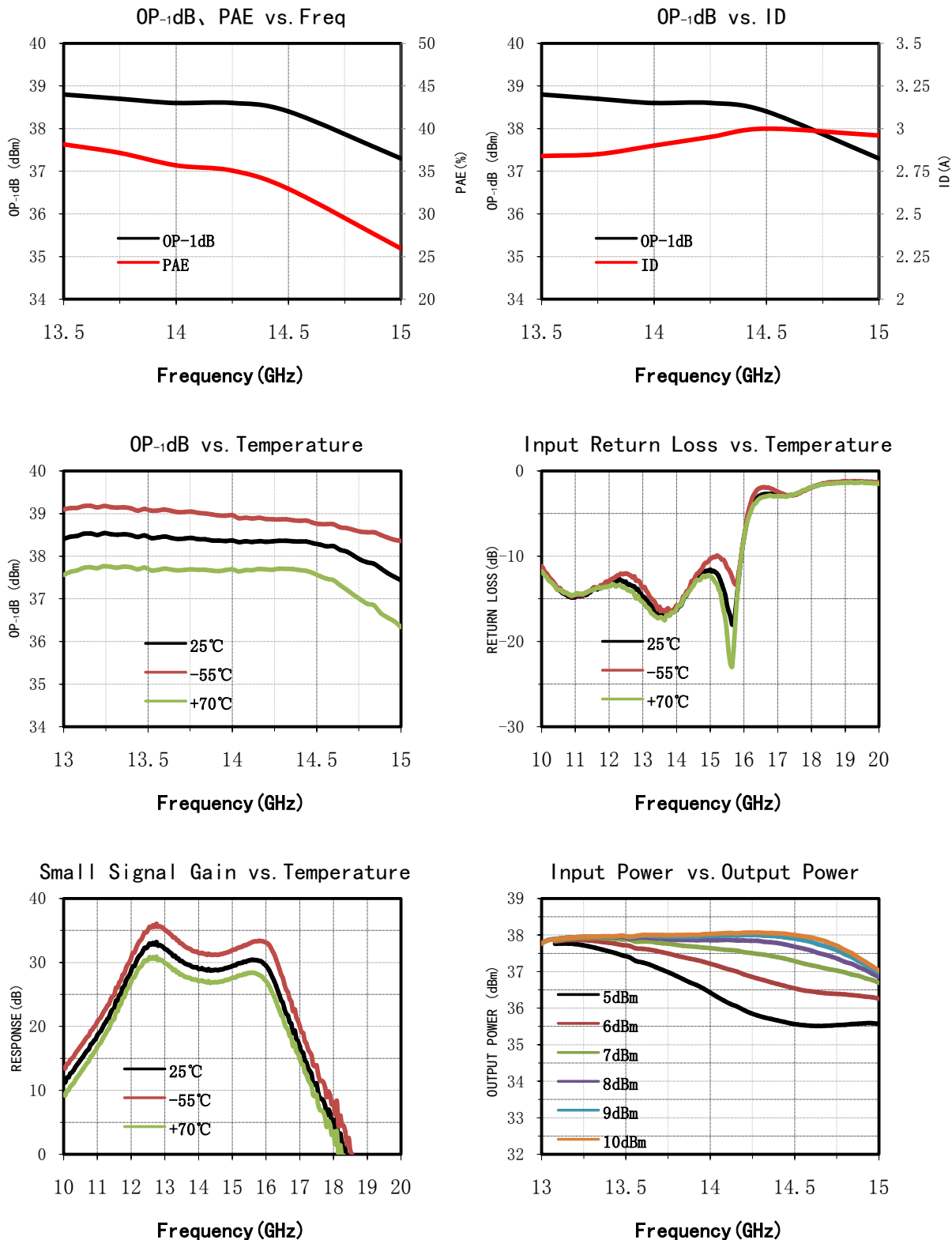
*** f=14.25GHz, VDS=7V, IDQ=2.45A, 8PSK, σ=0.5, symbol rate=2M

ABSOLUTE MAXIMUM RATINGS

CW Input Power	+20dBm	Operating Temperature	-55°C~+85°C
Junction Temperature	150°C	Storage Temperature	-65°C~+150°C
Drain Supply Voltage	+9V	Gate Supply Voltage	-2V
ESD (HBM)	Class 1A	Output Mismatch Stress	3:1
Soldering Temperature	260°C, 20s		

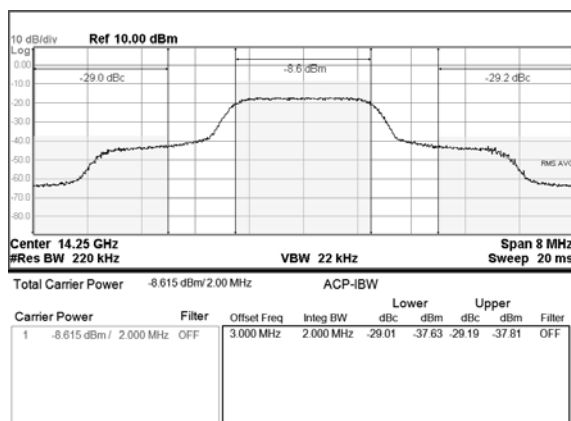


Typical Performance

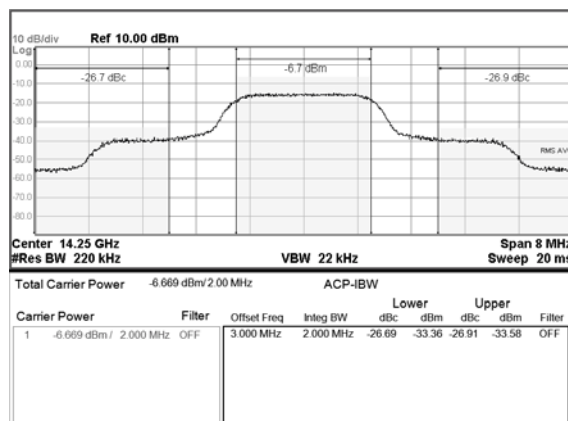
VD=+7V IDQ=2.25A T_A=25°C CW Operation

ACPR Performance

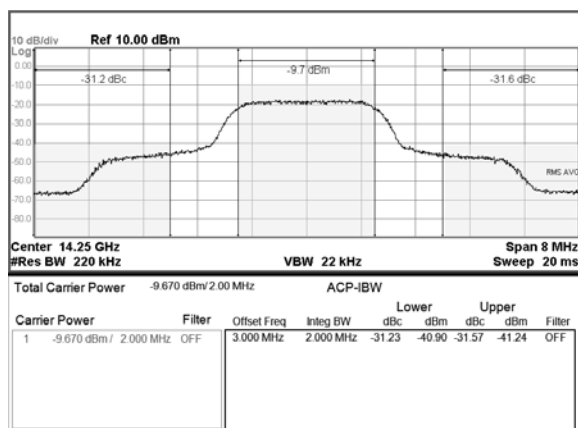
P_{OUT}=36dBm IDQ=2.25A



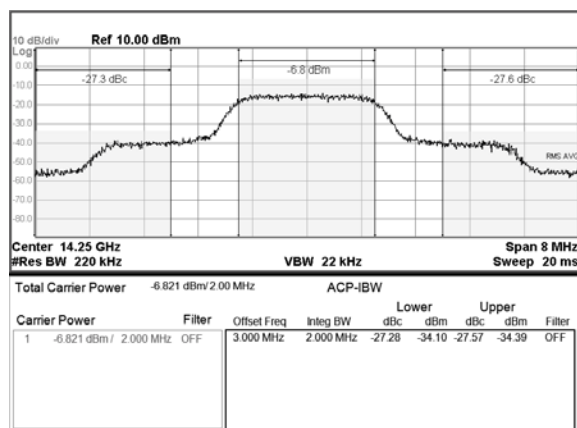
P_{OUT}=37dBm IDQ=2.25A



P_{OUT}=36dBm IDQ=2.45A



P_{OUT}=37dBm IDQ=2.45A



EVM Performance

P_{OUT}=36.5dBm IDQ=2.25A

EVM	= 6.6896	%rms	17.756	% pk at sym	849
Mag Err	= 4.4720	%rms	-14.371	% pk at sym	576
Phase Err	= 2.8820	%rms	9.2286	deg pk at sym	849
Freq Err	= -36.173	Hz	SNR (MER) =	23.492	dB
IQ Offset	= -34.873	dB	Amp Droop =	-76.42	udB/sym
Quad Err	= 27.712	mdeg	Gain lmb	= -0.007	dB
0	01010111	00110101	11011110	11010101	01101000 00000101
48	01000110	00000110	10110110	00111000	01101111 10100110
96	10010101	11010101	10000101	11101110	00111000 10011110
144	01000110	01111110	10100010	01100110	01110100 10000001
192	00100110	10111110	10110000	10010100	10111110 00100101
240	10111000	11010101	01000100	11110000	01000001 01010101
288	11001110	00101111	11111101	10010010	00001100 00010110

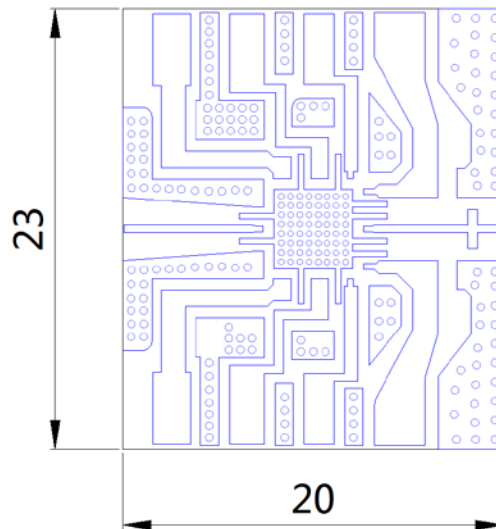
P_{OUT}=36.5dBm IDQ=2.45A

EVM	= 5.9975	%rms	16.463	% pk at sym	994
Mag Err	= 4.2154	%rms	-14.947	% pk at sym	234
Phase Err	= 2.4684	deg	8.6854	deg pk at sym	530
Freq Err	= -34.182	Hz	SNR(MER)	= 24.441	dB
IQ Offset	= -36.336	dB	Amp Droop	= -29.45	udB/sym
Quad Err	= -27.011	mdeg	Gain lmb	= 0.056	dB
0	10101110	11111010	10100111	10101110	01101001 01010111
48	10001001	11111001	11111110	10110100	10110000 11000111
96	00101000	01101100	10110111	00010100	10011001 00011000
144	11100010	11000101	10010111	00001010	10000111 01011111
192	01101001	00111111	11110110	11000110	01100110 11101010
240	11001001	10010011	10110001	00101110	01111110 10010010
288	10001100	01111100	00110001	11001000	11011011 10101011





Recommended PCB Layout



1.Unit: millimeters

2.PCB : Rogers. RO 4003c t=0.203

Operating the XT3110Q6

- 1.The XT3110Q6 is biased with a positive drain power supply and negative gate power supply. Performance is optimized at the drain voltage setting to +7.0V, The recommended quiescent drain current is 2.25Amps.
- 2.Turn ON procedure:
 - a.Apply gate voltage V_G and set to -0.8 V
 - b.Apply drain voltage V_D and set to +7 V
- 3.Turn OFF procedure:
 - a.Turn off drain voltage V_D
 - b.Turn off gate voltage V_GRF power can be applied at any time.
- 4.To improve the thermal and RF performance, we recommend attach a heat sink to the bottom of the board and apply 0.1mm indium shim between the heat sink and the board.